

**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ/T 11829.2-2022

**Plasma Enhanced Chemical Vapor Deposition (PECVD)
Equipment for Crystalline Silicon Photovoltaic Cells - Part 2:
Plate PECVD Equipment**

晶体硅光伏电池用等离子体增强化学气相淀积（PECVD）设备 第2部分：板式 PECVD 设备

(English Translation)

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What this standard covers

This standard specifies the terms and definitions, model designation, working environment, requirements, inspection methods, inspection rules, and packaging, marking, handling, transportation, and storage of plate-type plasma-enhanced chemical vapor deposition (PECVD) equipment for crystalline silicon photovoltaic cells. . Suitable for plate type PECVD equipment for crystalline silicon photovoltaic cells. This document is applicable to the deposition of various thin film materials such as amorphous silicon (a-Si:H), microcrystalline silicon (μc-Si:H), silicon dioxide (SiO₂), aluminum oxide (Al₂O₃), silicon nitride Intrinsic thin films such as (SiN_x) thin films and various doped thin film materials, etc. PECVD equipment for thin-film photovoltaic cells and flexible photovoltaic cells can also be used as a reference.

Document data

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